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[KR/KR]; 6-803 Taeneung-Woosung Apt., Kongneung
2-Dong, Nowon-Ku, Seoul 139-242 (KR). KIM, Hyo-Tae
[KR/KR]; 36, KIST Dormitory, 39-1 Hawolgok-Dong,
Sungbook-Ku, Seoul 136-791 (KR).

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(74) Agent: PARK, Jang-Won; 5th Floor, Jewoo Building,
200, Nonhyun-Dong, Kangnam-Ku, Seoul 135-010 (KR).

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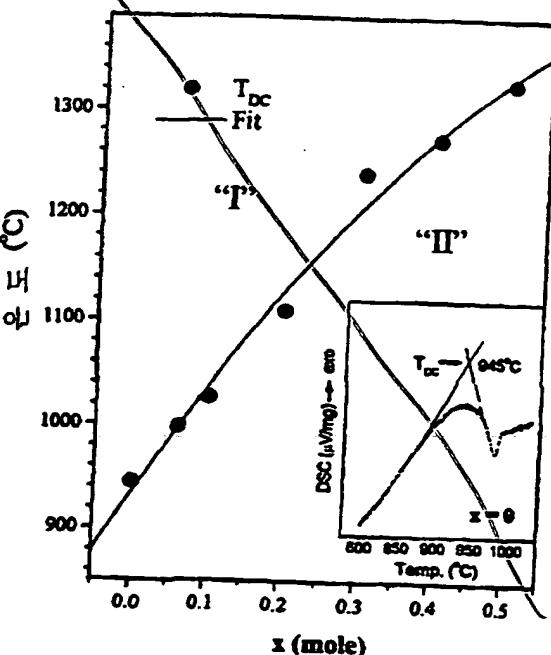
(71) Applicant (for all designated States except US): KOREA
INSTITUTE OF SCIENCE AND TECHNOLOGY
[KR/KR]; 39-1, Hawolgok-Dong, Sungbook-Ku, Seoul
136-791 (KR).

(72) Inventors; and

(75) Inventors/Applicants (for US only): KIM, Yoon-Ho

MM
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(54) Title: LOW TEMPERATURE SINTERABLE AND LOW LOSS DIELECTRIC CERAMIC COMPOSITIONS AND
METHOD THEREOF



(57) Abstract: A low loss high-frequency dielectric ceramic composition for sintering at a low temperature and method of manufacturing the same which is characterized in that excellent dielectric properties such as a much lower sintering temperature and higher quality coefficient and dielectric constant, compared to a conventional high-frequency ceramic composition, a stabilized temperature coefficient, and a temperature compensating property varied according to a composition, are implemented using a low-priced material such as ZnO-MO (M=Mg, Co, Ni) - TiO₂. In addition, Ag, Cu, an alloy thereof, or an Ag/Pd alloy can be used as an internal electrode. Thus, the composition of the present invention can be used as a dielectric material for all sorts of high-frequency devices, such as a stacked chip capacitor, stacked chip filter, stacked chip capacitor/inductor composite device and module, low temperature sintered substrate, resonator or filter and ceramic antenna.

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